

IN THE SPECIFICATION:

Please amend paragraph [0008] as follows:

[0008] One embodiment comprises a method including introducing at least one gaseous aluminum compound into the halogen-containing environment. The at least one gaseous aluminum compound may be a trialkylaluminum compound, an alane, an alkylaluminum hydride, an alkylaluminum halide, an alkylaluminum sesquihalide, or an aluminum sesquihalide. For instance, trimethyl aluminum (TMA), triethyl aluminum, triisobutyl aluminum, ~~triethyl(tri-sec-butoxy)dialuminum~~ triethyl(tri-sec-butoxy)dialuminum (TETBOL), or tritertiarybutyl aluminum may be used as the at least one gaseous aluminum compound. The at least one gaseous aluminum compound is reacted with at least one halogenated material to form a gaseous reaction product, which is subsequently removed from the environment. The gaseous reaction product may be removed by venting the environment or applying a vacuum to the environment.

Please amend paragraph [0015] as follows:

[0015] In order to facilitate a better understanding and appreciation for the nature of the problems addressed by the present invention and not by way of limitation thereof, FIG. 1 ~~of the drawings~~ schematically depicts an exemplary deposition chamber 10 suitable for use in, for example, CVD processes. Deposition chamber 10 includes a showerhead 12 disposed over a heater stage 14 carrying a semiconductor substrate 16 such as, for the sake of discussion and not limitation of the invention, a silicon wafer. Input port 18 is used to introduce one or more precursor gases into the interior 20 of deposition chamber 10 through showerhead 12. Semiconductor substrate 16 may be maintained at a desired, elevated temperature by heater stage 14, which is selectively variable in heat output. The one or more precursor gases flowing into the interior 20 of deposition chamber 10 include a material component or combination of components to be deposited as a film on semiconductor substrate 16. However, because the deposition process is nonspecific to semiconductor substrate 16, a film of the material component or combination is also undesirably deposited on heater stage 14 as well as on ~~sidewalls~~ side walls 22, bottom wall 24 and top wall 26 and other surfaces present within the

interior 20 of deposition chamber 10. Outlet port 28, used to exhaust gases from the interior 20 of deposition chamber 10, may also have its interior undesirably coated with a film of the component or combination. As noted previously, when a deposition chamber such as deposition chamber 10 is cleaned using conventional techniques to remove the component or combination, a halogenated environment may result and halogenated compounds are undesirably formed on the interior surfaces of deposition chamber 10 and associated equipment.

Please amend paragraph [0016] as follows:

[0016] The aluminum compound may be a liquid or a gas, depending on temperature and/or pressure conditions present in the interior 20 of deposition chamber 10. Desirably, the aluminum compound is introduced into the interior 20 of deposition chamber 10 through, for example, input port 18 and showerhead 12 in a gaseous or vapor state, the former term as used herein including the latter, so that it fully penetrates the ~~deposition-chamber~~ chamber 10 and contacts the halogenated materials, such as those adsorbed to the interior surfaces of the ~~deposition-chamber~~ chamber 10 on-side-walls sidewalls 22, bottom wall 24 and top wall 26. However, the aluminum compound may also be introduced into the deposition chamber as a liquid, such as by using jets or atomizers (not shown). The liquid aluminum compound may then be converted into a gaseous state in deposition chamber 10 by maintaining the interior 20 of deposition chamber 10 at conditions sufficient to gasify the aluminum compound.